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# FQP19N20C / FQPF19N20C

## N-Channel QFET® MOSFET

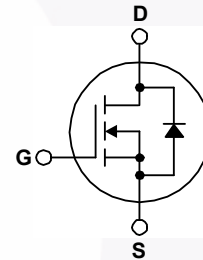
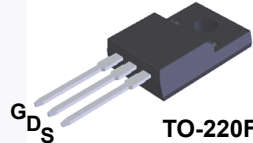
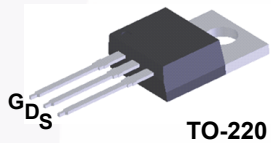
200 V, 19 A, 170 mΩ

### Features

- 19 A, 200 V,  $R_{DS(on)} = 170 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 9.5 \text{ A}$
- Low Gate Charge (Typ. 40.5 nC)
- Low Crss (Typ. 85 pF)
- 100% Avalanche Tested

### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQP19N20C	FQPF19N20C	Unit
$V_{DSS}$	Drain to Source Voltage	200		V
$I_D$	Drain Current	-Continuous ( $T_C = 25^\circ\text{C}$ )	19.0	19.0 *
		-Continuous ( $T_C = 100^\circ\text{C}$ )	12.1	12.1 *
$I_{DM}$	Drain Current - Pulsed (Note 1)	76.0	76.0 *	A
$V_{GSS}$	Gate to Source Voltage	$\pm 30$		V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	433		mJ
$I_{AR}$	Avalanche Current (Note 1)	19.0		A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	13.9		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5		V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	139	43	W
		1.11	0.34	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

\*Drain current limited by maximum junction temperature

### Thermal Characteristics

Symbol	Parameter	FQP19N20C	FQPF19N20C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.9	2.89	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	62.5	62.5	$^\circ\text{C}/\text{W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQP19N20C	FQP19N20C	TO-220	Tube	N/A	50 units
FQPF19N20C	FQPF19N20C	TO-220F	Tube	N/A	50 units

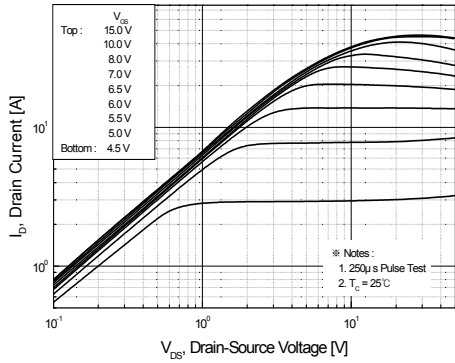
## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
<b>Off Characteristics</b>							
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	200	--	--	V	
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.24	--	$\text{V}/^\circ\text{C}$	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$	
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$	
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA	
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA	
<b>On Characteristics</b>							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 9.5\text{ A}$	--	0.14	0.17	$\Omega$	
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 9.5\text{ A}$	--	10.8	--	S	
<b>Dynamic Characteristics</b>							
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	830	1080	pF	
$C_{oss}$	Output Capacitance		--	195	255	pF	
$C_{rss}$	Reverse Transfer Capacitance		--	85	110	pF	
<b>Switching Characteristics</b>							
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 19.0\text{ A},$ $R_G = 25\ \Omega$	--	15	40	ns	
$t_r$	Turn-On Rise Time		--	150	310	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4)	--	135	280	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	115	240	ns
$Q_g$	Total Gate Charge	$V_{DS} = 160\text{ V}, I_D = 19.0\text{ A},$ $V_{GS} = 10\text{ V}$	--	40.5	53.0	nC	
$Q_{gs}$	Gate-Source Charge		(Note 4)	--	6.0	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	22.5	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>							
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	19.0	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	76.0	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 19.0\text{ A}$	--	--	1.5	V	
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 19.0\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	208	--	ns	
$Q_{rr}$	Reverse Recovery Charge		--	1.63	--	$\mu\text{C}$	

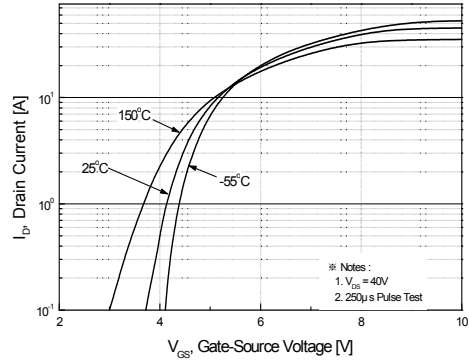
### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2.  $L = 1.8\text{ mH}, I_{AS} = 19.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 19.0\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

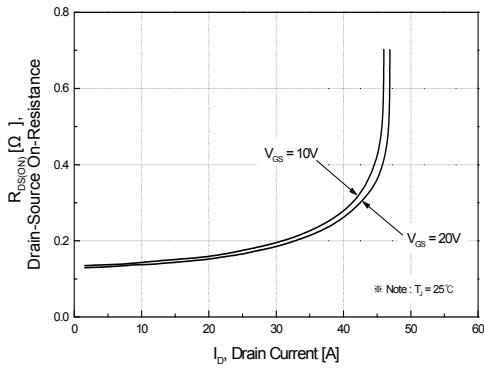
## Typical Characteristics



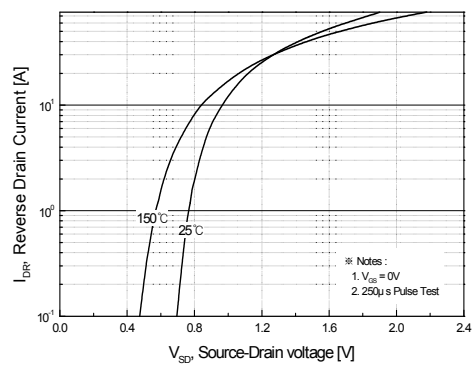
**Figure 1. On-Region Characteristics**



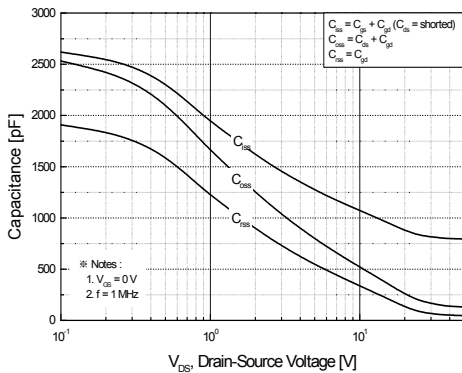
**Figure 2. Transfer Characteristics**



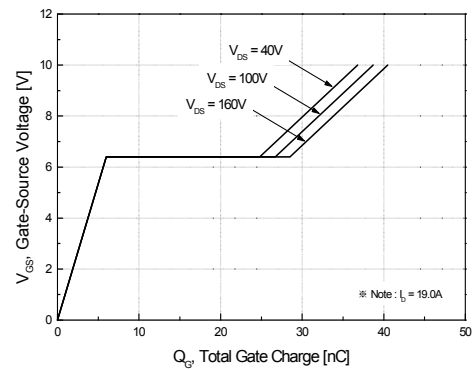
**Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**

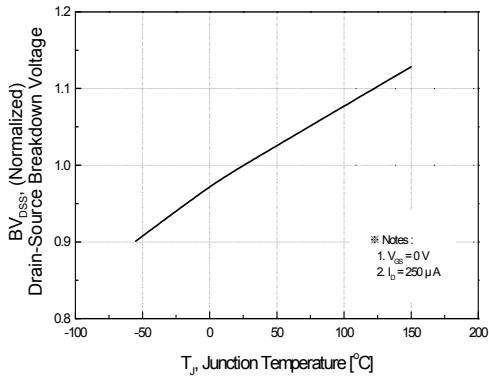


**Figure 5. Capacitance Characteristics**

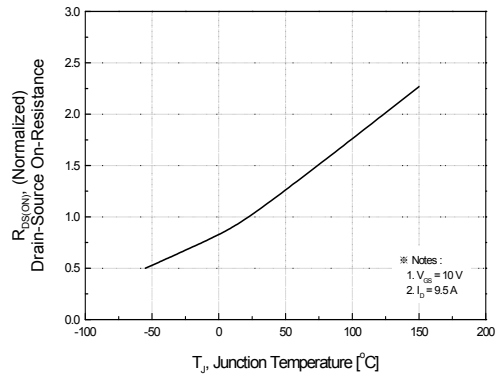


**Figure 6. Gate Charge Characteristics**

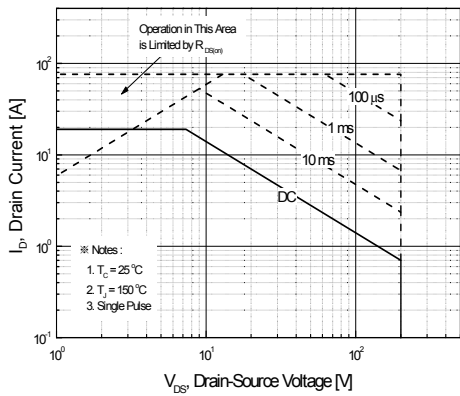
**Typical Characteristics** (Continued)



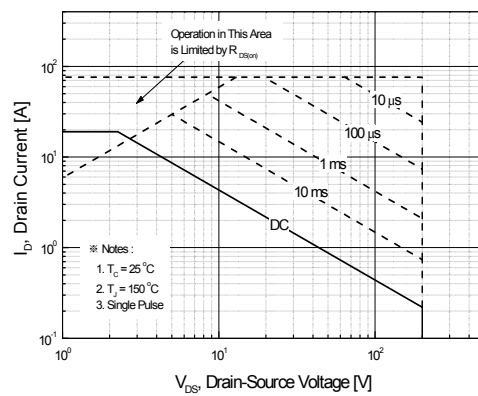
**Figure 7. Breakdown Voltage Variation vs Temperature**



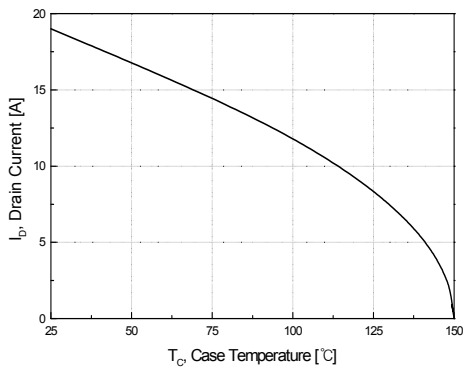
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9-1. Maximum Safe Operating Area for FQP19N20C**

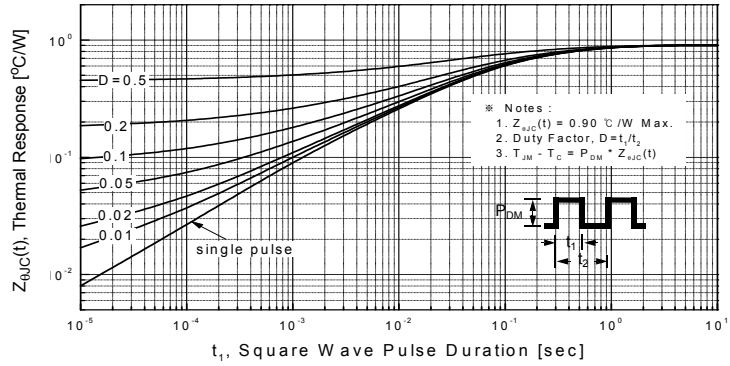


**Figure 9-2. Maximum Safe Operating Area for FQPF19N20C**

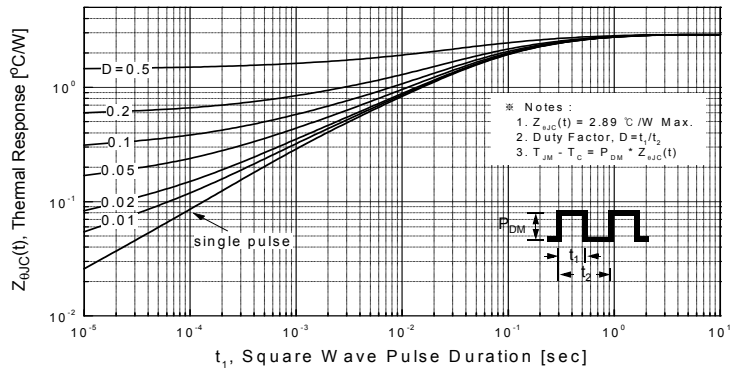


**Figure 10. Maximum Drain Current vs Case Temperature**

**Typical Characteristics** (Continued)

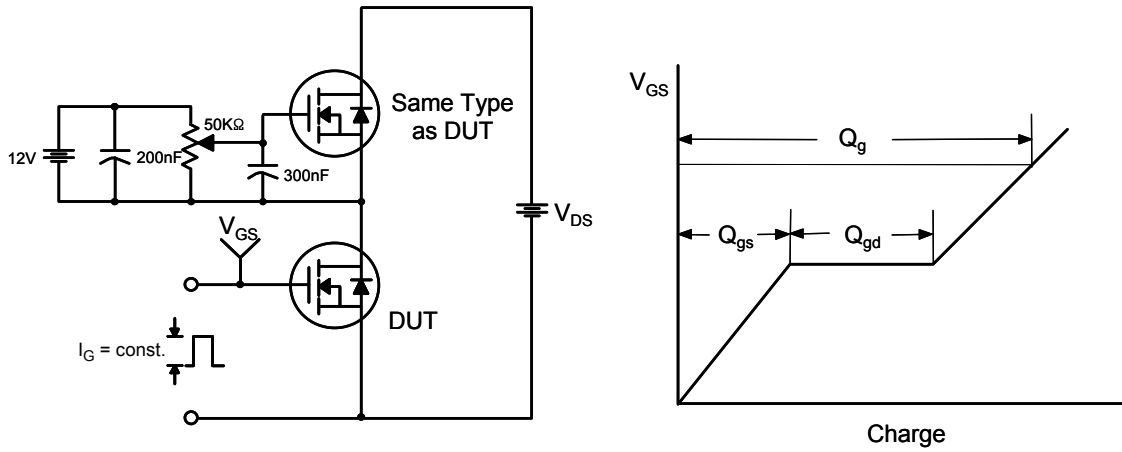


**Figure 11-1. Transient Thermal Response Curve for FQP19N20C**

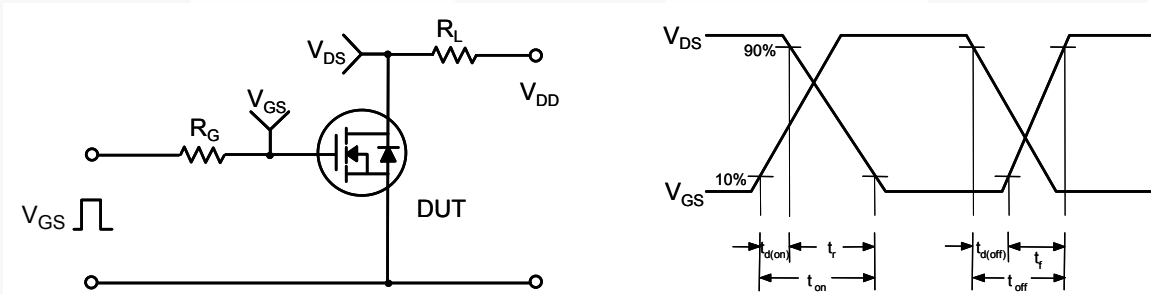


**Figure 11-2. Transient Thermal Response Curve for FQPF19N20C**

**Figure 12. Gate Charge Test Circuit & Waveform**



**Figure 13. Resistive Switching Test Circuit & Waveforms**



**Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms**

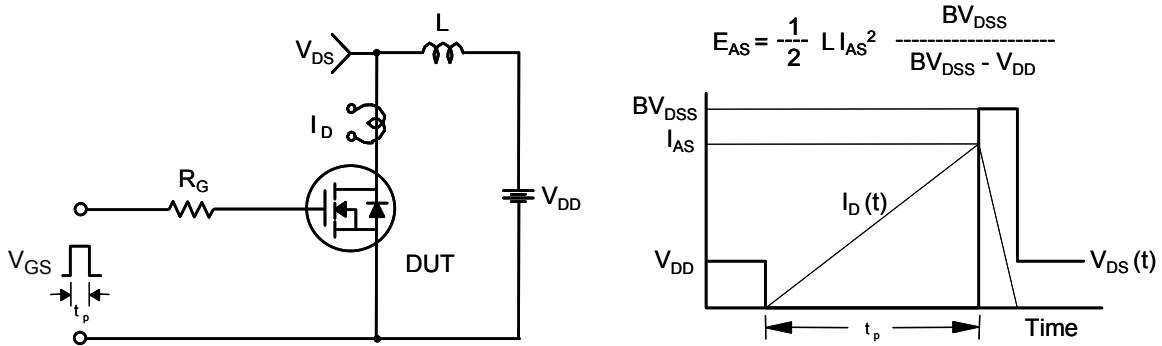
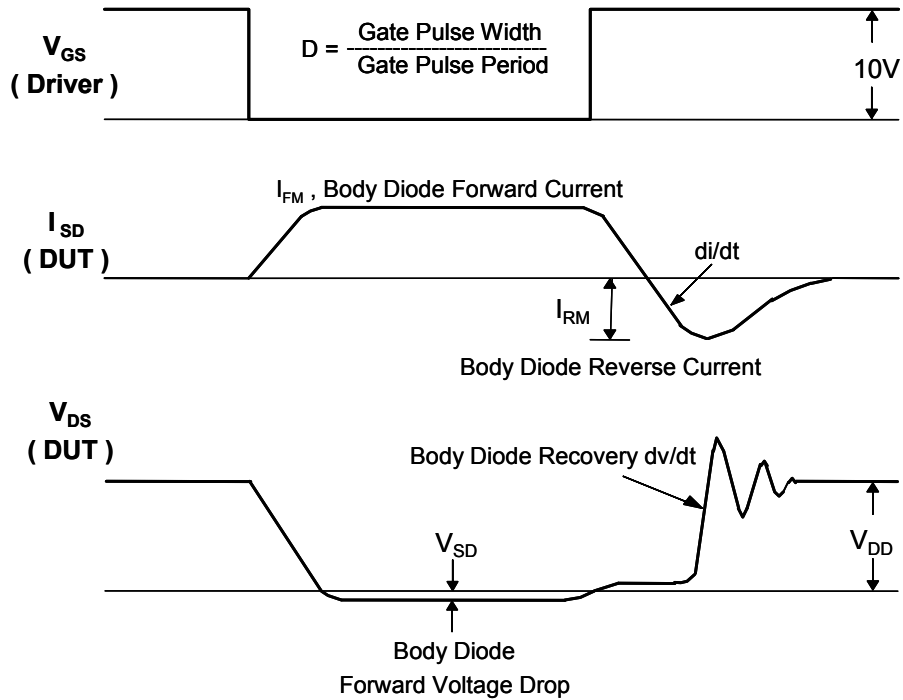
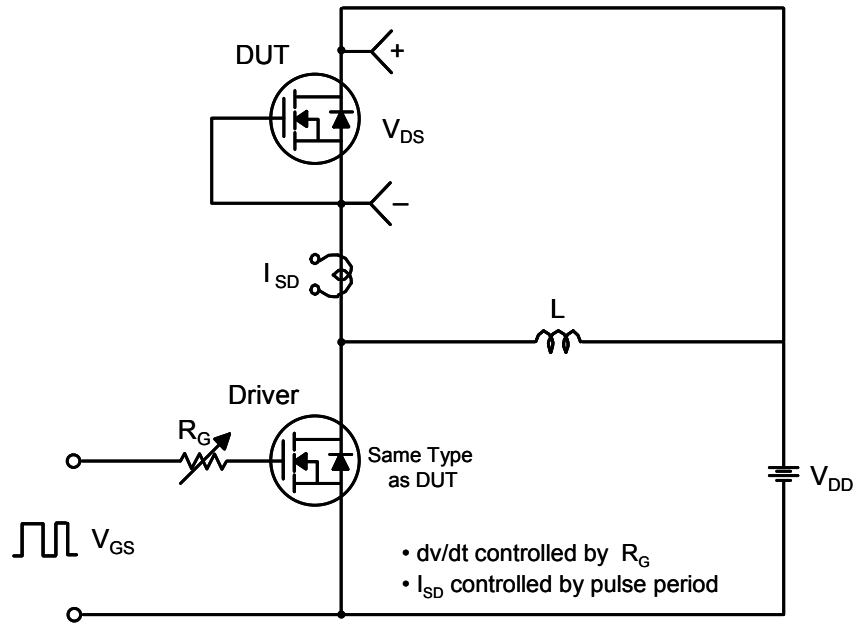
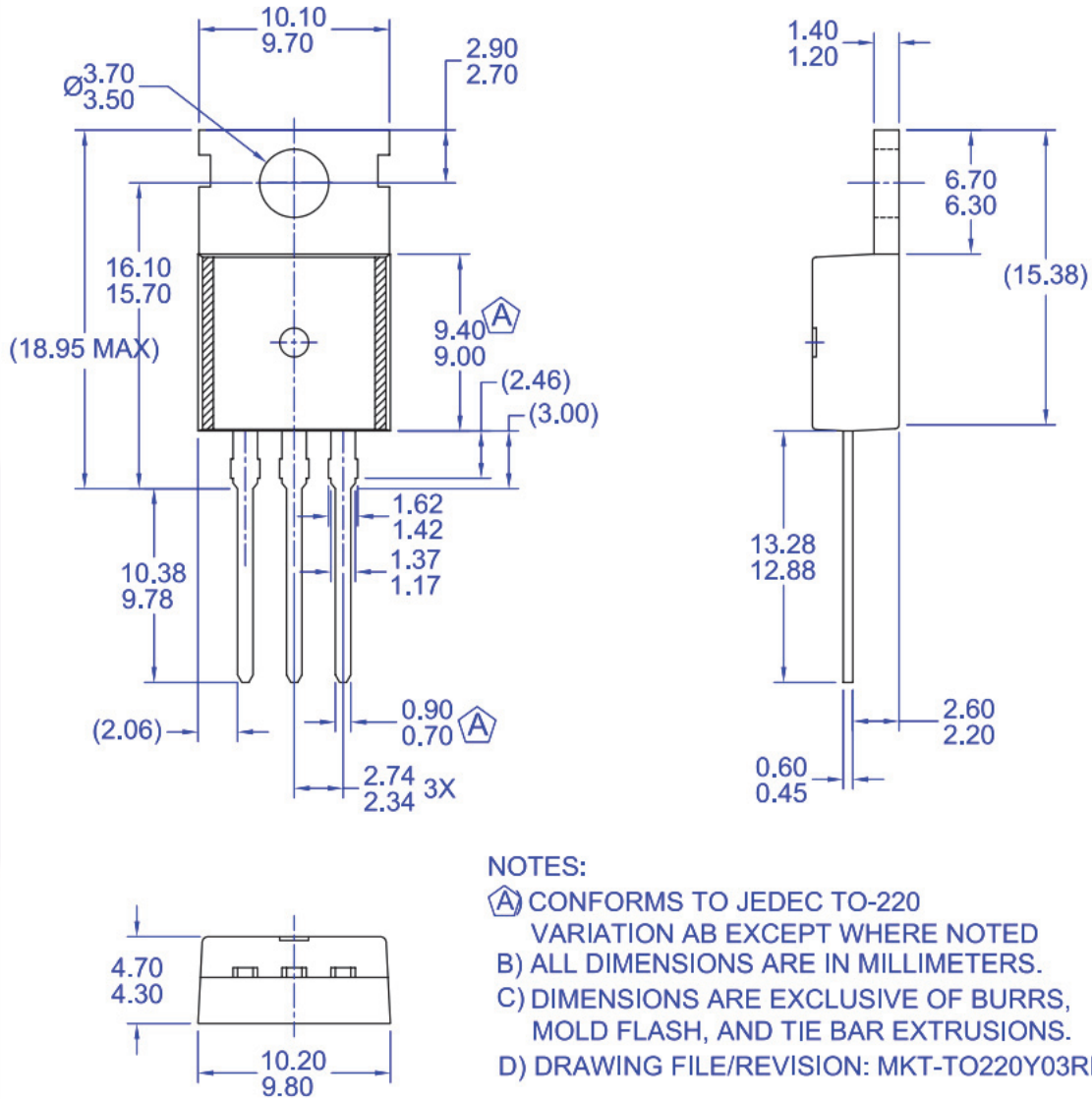


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





## Mechanical Dimensions



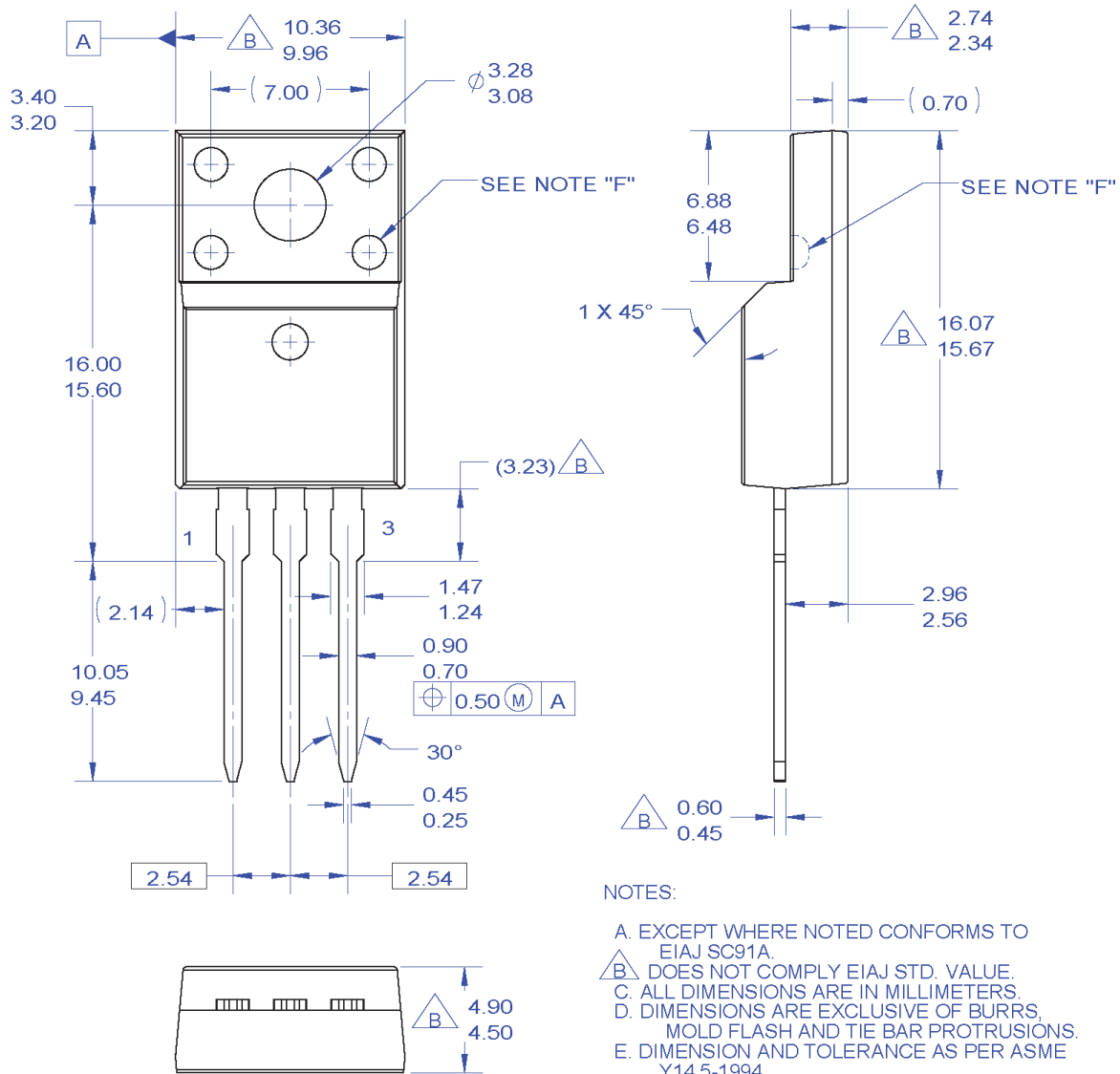
**Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB**

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## Mechanical Dimensions



### NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.  
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

**Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead**

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| Build it Now™            | GreenBridge™                                    | TinyBuck®                |
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|                          | PowerXS™  |                          |
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|                          | SuperSOT™-6                                     |                          |
|                          | SuperSOT™-8                                     |                          |
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